

InGaAs PIN PHOTODIODE**PD-1170N****3 mm InGaAs PIN Photodiode with TO-5 Package****FEATURES**

- ◇ High responsivity for dual windows at 1310 nm and 1550 nm
- ◇ Low dark current
- ◇ Hermetically sealed TO-5 3-pin metal case
- ◇ Active diameter 3 mm
- ◇ No AR Coating, Flat Window Cap Package

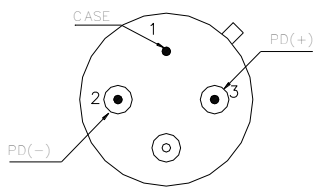
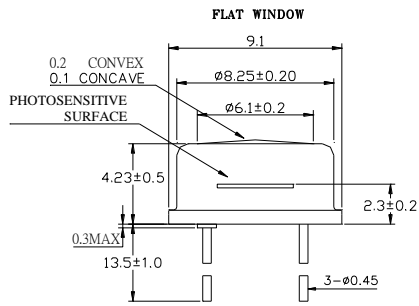
DESCRIPTION

PD-1170N InGaAs Photodiode are suited to receive the light at the wavelength range from 800 nm to 1650 nm. With high reliability, PD-1170N series are the best choice for power monitor application.

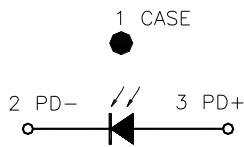
ELECTRICAL AND OPTICAL CHARACTERISTICS (T _c =25°C)						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			3		mm
	Detection Range		800		1650	nm
R	Responsivity	V _R =3V, λ=1300 nm	0.79	0.84		A/W
		V _R =3V, λ=1550 nm	0.84	0.93		
I _{dark}	Dark Current	V _R =3V			50	nA
C	Capacitance	V _R =3V		750	1800	pF
	Shunt Resistance	V _R =10mV	1	10		MΩ

ABSOLUTE MAXIMUM RATINGS (T _c =25 °C)			
Symbol	Parameter	Ratings	Unit
P _o	Input Optical Power	10	mW
V _{RD}	Reverse Voltage	5	V
I _{FD}	Forward Current	10	mA
T _{opr}	Operating Temperature	-40~+85	°C
T _{stg}	Storage Temperature	-40~+85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



BOTTOM VIEW



Note: 1. Specifications subject to change without notice.

ORDER INFORMATION

Part No.: P D - 1 1 7 0 N

Revision History

Version	Subject	Release Date
1.0	Initial datasheet	2/16/2023